SGS-THOMSON MICROELECTRONICS

STTB6006T(V)1/2

TURBOSWITCH ™ "B". ULTRA-FAST HIGH VOLTAGE DIODE

MAIN PRODUCTS CHARACTERISTICS

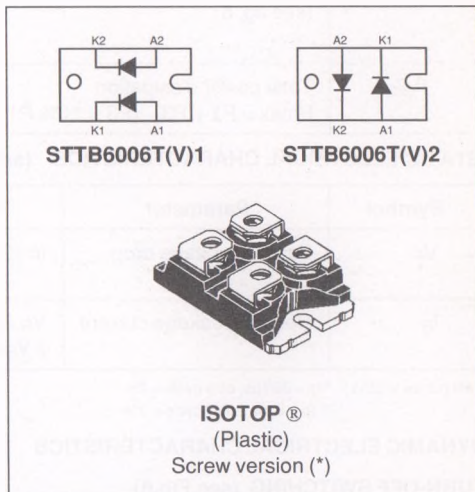| $I_{F(AV)}$	2*30A
V_{RRM}	600V
t_{rr} (typ)	60ns
V_F (max)	1.3V

FEATURES AND BENEFITS

- SPECIFIC TO THE FOLLOWING OPERATIONS: Snubbing or clamping, demagnetization and rectification.
- ULTRA-FAST, SOFT AND NOISE-FREE RECOVERY.
- VERY LOW OVERALL POWER LOSSES AND PARTICULARITY LOW FORWARD VOLTAGE.
- DESIGNED FOR HIGH PULSED CURRENT OPERATIONS.

STTB6006T(V)1   STTB6006T(V)2

ISOTOP ®
(Plastic)
Screw version (*)

DESCRIPTION

The TURBOSWITCH is a very high performance series of ultra-fast high voltage power diodes from 600V to 1200V.
TURBOSWITCH, B family, drastically cuts losses in all high voltage operations which require extremely fast, soft and noise-free power diodes. They are particularly suitable in the primary circuit of an SMPS as snubber, clamping or demagnetizing diodes, and also in most power converters as high performance rectifier diodes. Packaged in ISOTOP these 600V devices are particularly intended for use on 240V domestic mains.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive peak reverse voltage	600	V
V_{RSM}	Non repetitive peak reverse voltage	600	V
$I_{F(RMS)}$	RMS forward current	50	A
I_{FRM}	Repetitive peak forward current (tp = 5 µs, f = 1kHz)	700	A
T_j	Max operating junction temperature	-65 to 150	°C
T_{stg}	Storage temperature	-65 to 150	°C

(*) : Tin plated Fast-on version is also available (without V suffix).

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THERMAL AND POWER DATA

Symbol	Parameter	Conditions		Value	Unit
$R_{th(j-c)}$	Junction to case thermal resistance	Per diode			˚C/W
		Total			
		Coupling			
P_1	Conduction power dissipation (see fig. 5)	Per diode $I_{F(AV)} = 30A$ $\delta = 0.5$ $T_C = 74˚C$			W
P_{max}	Total power dissipation Pmax = P1 + P3 (P3 = 10% P1)	Per diode $T_C = 66˚C$			W

STATIC ELECTRICAL CHARACTERISTICS   (see Fig.5)

Symbol	Parameter	Test Conditions		Min	Typ	Max	Unit
V_F •	Forward voltage drop	$I_F = 30A$	$T_j = 25˚C$			1.4	V
			$T_j = 125˚C$			1.3	V
I_R ••	Reverse leakage current	$V_R = 0.8$ x V_{RRM}	$T_j = 25˚C$			150	μA
			$T_j = 125˚C$			5	mA

Test pulses widths :   * tp = 380 μs, duty cycle < 2%
                          ** tp = 5 ms , duty cycle < 2%

DYNAMIC ELECTRICAL CHARACTERISTICS

TURN-OFF SWITCHING (see Fig.6)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
t_{rr}	Reverse recovery time	$T_j = 25˚C$ $I_F = 0.5 A$ $I_R = 1A$ Irr = 0.25A $I_F = 1 A$ $dI_F/dt = -50A/μs$ $V_R = 30V$		60	110	ns
I_{RM}	Maximum reverse recovery current	$T_j = 125˚C$ VR = 400V $I_F = 30A$ $dI_F/dt = -240 A/μs$ $dI_F/dt = -500 A/μs$	TBD	TBD		A
S factor	Softness factor	$T_j = 125˚C$ $V_R = 400V$ $I_F = 30A$ $dI_F/dt = -240 A/μs$ $dI_F/dt = -500 A/μs$		TBD TBD		/

TURN-ON SWITCHING   (see Fig.7)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
t_{fr}	Forward recovery time	$T_j = 25˚C$ $I_F = 30 A$, $dI_F/dt = 240 A/μs$ measured at, $1.1 \times V_F max$			TBD	ns
V_{Fp}	Peak forward voltage	$T_j = 25˚C$ $I_F = 30A$, $dI_F/dt = 240 A/μs$ $I_F = 150A$, $dI_F/dt = 500 A/μs$		TBD TBD		V

TBD : To Be Defined

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APPLICATION DATA

The TURBOSWITCH "B" is especially designed to provide the lowest overall power losses in any application such as snubbing,clamping, demagnetization and rectification. In such applications (fig.1 to fig.4), the way of calculating the power losses is given below :
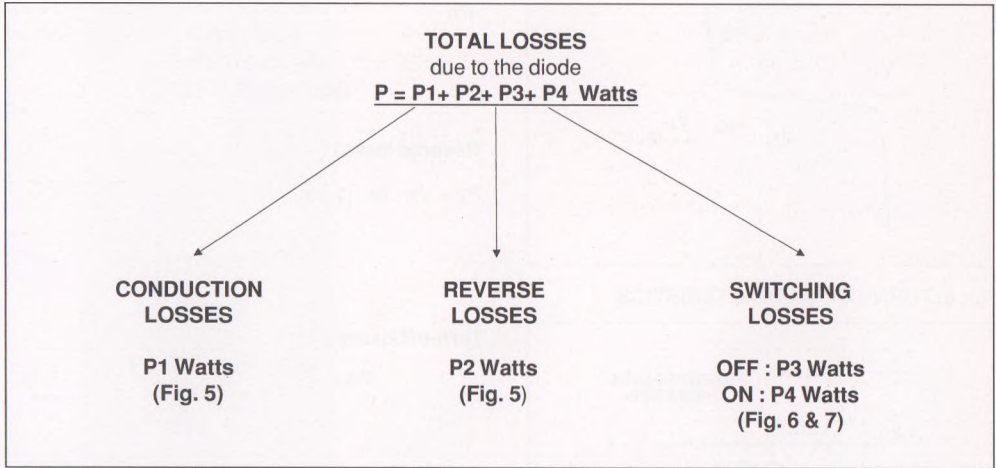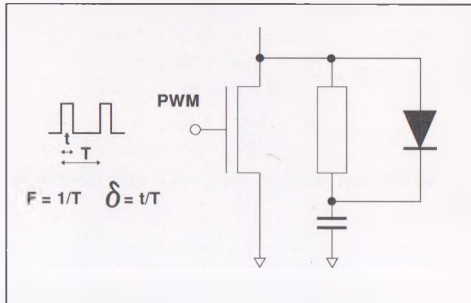
TOTAL LOSSES
due to the diode
P = P1+ P2+ P3+ P4 Watts

CONDUCTION LOSSES	REVERSE LOSSES	SWITCHING LOSSES
P1 Watts (Fig. 5)	**P2 Watts** (Fig. 5)	**OFF : P3 Watts** **ON : P4 Watts** (Fig. 6 & 7)

Fig. 1 : SNUBBER DIODE.

Fig. 2 : CLAMPING DIODE.
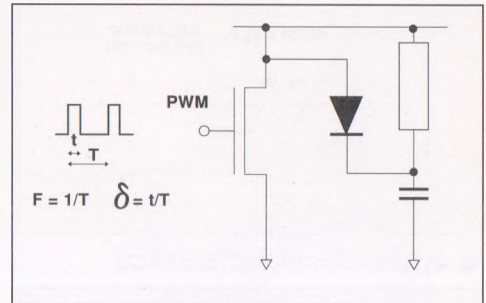
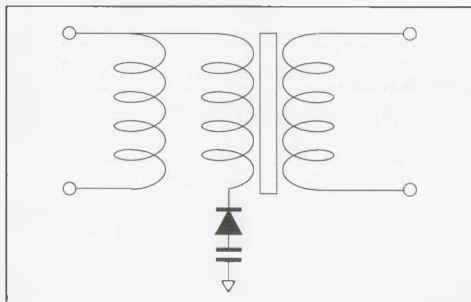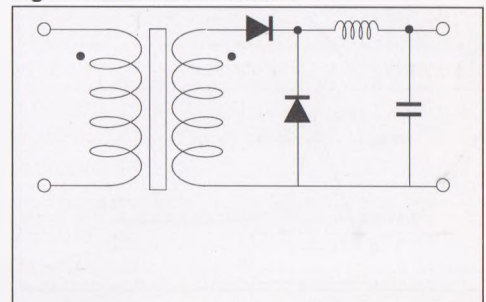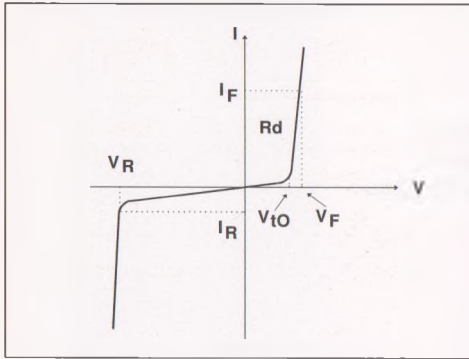**Fig. 3 :** DEMAGNETIZING DIODE.

Fig. 4 : RECTIFIER DIODE.

APPLICATION DATA (Cont'd)

Fig. 5: STATIC CHARACTERISTICS

Conduction losses :

$$P1 = V_{t0} . I_{F(AV)} + R_d . I_F{}^2{}_{(RMS)}$$

with

$$V_{t0} = 1.00 \ V$$
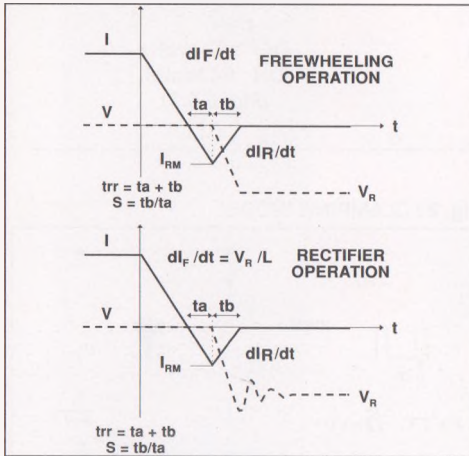$$R_d = 0.010 \ Ohm$$
(Max values at 125°C)

Reverse losses :

$$P2 = V_R . I_R . (1 - \delta)$$

Fig. 6: TURN-OFF CHARACTERISTICS

Turn-off losses :

$$P3 = \frac{V_R \times I_{RM}{}^2 \times S \times F}{6 \ x \ dI_F/dt}$$
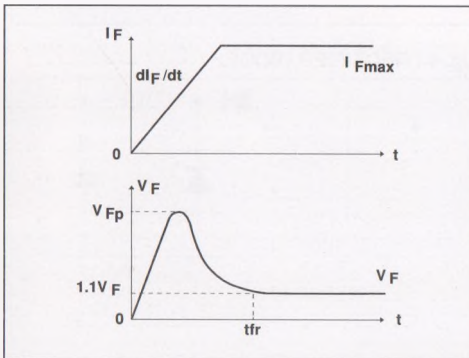
Turn-off losses :
(with non negligible serial inductance)

$$P3' = \frac{V_R \times I_{RM}{}^2 \times S \times F}{6 \ x \ dI_F/dt} + \frac{L \times I_{RM}{}^2 \times F}{2}$$

P3 and P3' are suitable for power MOSFET and IGBT

Fig. 7: TURN-ON CHARACTERISTICS

Turn-on losses :

$$P4 = 0.4 \ (V_{FP} - V_F) . I_{Fmax} . t_{fr} . F$$

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